

Silicon PNP Power Transistors

2SB677

DESCRIPTION

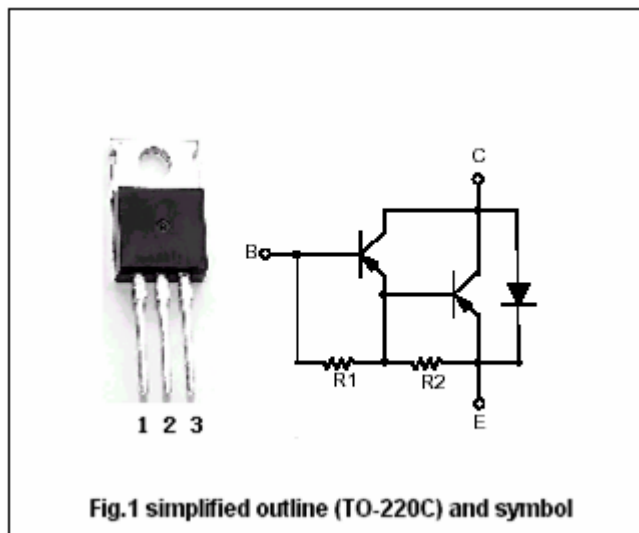
- With TO-220C package
- DARLINGTON
- High DC current gain
- Low collector saturation voltage

APPLICATIONS

- High power switching applications
- Power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-60	V
V _{CEO}	Collector-emitter voltage	Open base	-40	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-3	A
I _B	Base current		-0.2	A
P _C	Collector power dissipation	T _C =25°C	25	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA, I _B =0	-40			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A, I _B =-4mA			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A, I _B =-4mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-60V, I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-3.0	mA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-2V	2000			
h _{FE-2}	DC current gain	I _C =-3A ; V _{CE} =-2V	1000			

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PACKAGE OUTLINE

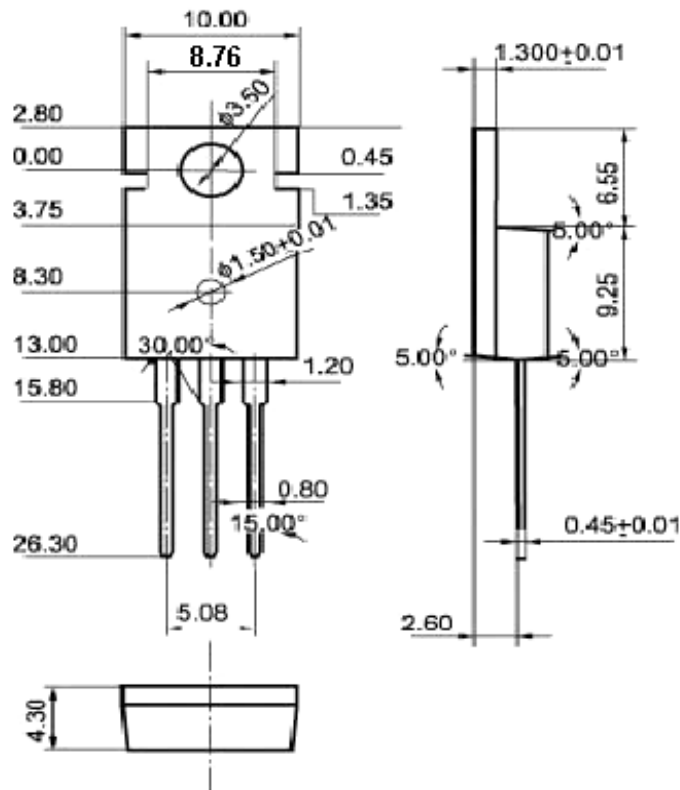


Fig.2 Outline dimensions